					DV		DATE	- 1		UNT	DESCE		OF RE		DV	СНК	ע ר	ATE
	DUNT	DESCRIPTION	OF REV	1210112	BY	CHKD				UNI	DESCR	RIPTION	N OF RE	1210102	BY			VIE.
]														
APPLI	CA	BLE STANDA	\RD															
OPERATING TEMPERATURE RA			NGE -55 C TO +85 C (note1) TE						TEM	ORAGE MPERATURE RANGE			−10℃ TO +60℃					
RATING VO		VOLTAGE		30 V AC/DC co						PLICABLE NNECTOR			BM23PF0.8-46DP-0.35V(**				∨(**)	
CURRENT			SIGNAL CONTACT 0.3A(note2) POWER CONTACT 5.0A															
	<u> </u>							FICA	TIC)N	S		-					
		ITEM	Τ		<u>TE</u>	ST MET			· · · ·		Ĭ	F	REQUIR	EMENT:	S		QT	AT
CONS	TRI	UCTION															<u> </u>	
GENERA	L EX	AMINATION	CONFIRMED VISUALLY AND BY MEASURING INSTRUMENT.								ACCORDING TO DRAWING.						x	x
MARKING	G		CONFI	rmed vi	ISUALL	.Y.			1						Х	х		
ELECT	<u>rric</u>	CAL CHARAG	CTERIS	STICS						· · · ·								
CONTAC	CT RE	ESISTANCE	20mV /	20mV AC OR LESS 1kHz, 1mA								SIGNAL CONTACT : 90m MAX POWER CONTACT : 30m MAX						_
	FION	RESISTANCE	100V DC								50MΩ MIN						X	-
	E PF	loof	100V AC FOR 1min.								NO FLASHOVER OR BREAKDOWN						Х	_
M€CH	IAN	ICAL CHARA	CTER	ISTICE	3													
			10 TIMES INSERTIONS AND EXTRACTIONS.								 CONTACT RESISTANCE: SIGNAL CONTACT : 90mΩ MAX POWER CONTACT : 30mΩ MAX NO DAMAGE, CRACK OR LOOSENESS OF PATRS. 						x	_
			SINGLE		TUDE 0	5 TO 10).75mm,		PROX 5m CLES,	nin		② NO D OF PA	Damage Arts.	ICAL DIS E, CRACH	(OR LOC	SENES	SS	x	-
上 Drese 通 CK				/s² DURA DIRECTI		OF PULS	;E 11 m;	s AT 3 TI	MES		@ NO E		ICAL DIS E, CRACH				x	_
		MENTAL CH									0, ,,	Anio.						
BAPID C	HAN										(f) CON	TACT R	ESISTAN	CE:			Т	
			TIME												AX			
der Xorr	nei			UNDER 5 CYCLES. (RELOCATION TIME TO CHAMBER: WITHIN2~3 MIN)								ER CO	NTACT : :	30mΩ M.	AX		x	
lication de ntact a con	a con a con			(TELECOATION TIME TO CHAMIDER. WITHINZ~3 MIN)									I RESIST		50MΩ		^	_
ntact	act											③ NO DAMAGE, CRACK OR LOOSENESS OF PARTS.						
<u>Б</u> Брабир н			EYPOS	EXPOSED AT 40±2℃, 90 TO 95%, 96h.								① CONTACT RESISTANCE:						
			EAFUU	EAF USED AT 4012 0, 90 10 95%, 901.								SIGNAL CONTACT : 90m MAX						
pleas												POWER CONTACT : 30m MAX						
ase mar n plea											② INSULATION RESISTANCE: 25MΩ MIN						X	-
292											③ NO DAMAGE, CRACK OR LOOSENESS							
	بر SULPHUR DIOXIDE			EXPOSED IN 25 PPM FOR 96h, 25℃, 75±5%RH.								ARTS.		<u></u>			–	
								/5±0%i	KH.				ESISTAN		Δχ			
			(10010	(Test standard : JIS C 60068)								SIGNAL CONTACT : 90mΩ MAX POWER CONTACT : 30mΩ MAX						_
												② NO DAMAGE, CRACK OR LOOSENESS						
											OF PARTS.							
REMARKS DRAWN								١		DESIGNED CHECKED APPROVED				D	RELEA	SED		
Note 1:	INCI		RATURE RISING BY CURRENT.							S.H.JUNG H.W.		н w.ic				ENG		
Note 2:	МАХ	(12A AT TOTAL I	PIN CONTACTS.					0.11.001							~ (17.05.10		
Unless otherwise specified, refer to JIS C 5402 and IEC							2	17.05.10			17.05.10 17.05.			10 17.05.10				ヮ
Note QT: QUALIFICATION TEST AT: ASSURANCE TEST X: APPLIC									ICAI	BLE	TEST							
										PART	NO.							
HIROSE KOREA CO.,LTD. SPECIFICATION SHEET BM23PF0.8-46DS-									SDS-	0.35	V(89	95)						
CODE N	0.(0	ID)		DRAWING NO.												$ ^{1}/$		
CL				SLC4-632258							CL 6644-0089-8-895							